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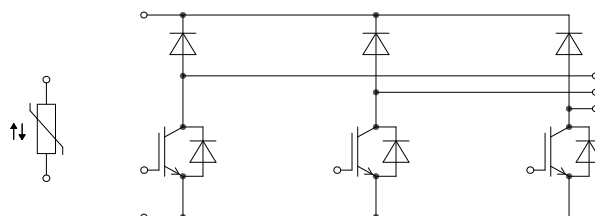
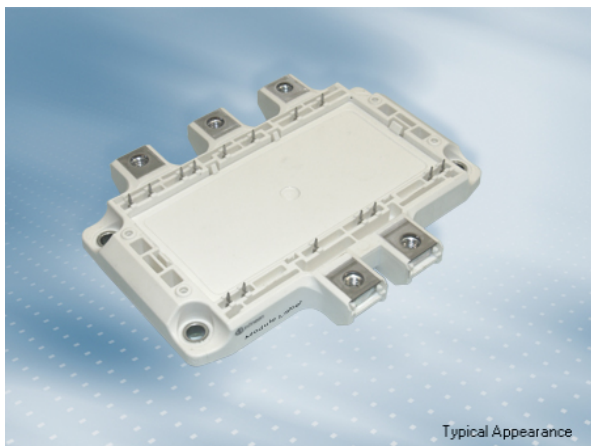
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



EconoPACK™4 Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled Diode und NTC
EconoPACK™4 module with trench/fieldstop IGBT4 and Emitter Controlled Diode and NTC



$V_{CES} = 1200V$
 $I_{C\ nom} = 200A / I_{CRM} = 400A$

Typische Anwendungen

- 3-Level-Applikationen
- Anwendungen mit hohen Schaltfrequenzen
- Chopper-Anwendungen
- Motorantriebe
- Solar Anwendungen
- USV-Systeme

Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur $T_{vj\ op}$
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} mit positivem Temperaturkoeffizienten

Mechanische Eigenschaften

- 2,5 kV AC 1min Isolationsfestigkeit
- Hohe mechanische Robustheit
- Integrierter NTC Temperatur Sensor
- Isolierte Bodenplatte
- Standardgehäuse

Typical Applications

- 3-Level-Applications
- High Frequency Switching Application
- Chopper Applications
- Motor Drives
- Solar Applications
- UPS Systems

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} with positive Temperature Coefficient

Mechanical Features

- 2.5 kV AC 1min Insulation
- High mechanical robustness
- Integrated NTC temperature sensor
- Isolated Base Plate
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

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IGBT, Brems-Chopper / IGBT, Brake-Chopper
Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	200 300	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	400	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	P_{tot}	1100	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 200\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 200\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 200\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,75 2,05 2,10	2,10	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	1,65			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	3,8			Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	12,5			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,54			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			0,015	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,185 0,20 0,205			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,037 0,044 0,046			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,365 0,455 0,475			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,044 0,072 0,078			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 4250\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	12,0 19,5 21,5			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3550\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	14,0 21,0 23,0			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	900			A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}			0,135	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,0645			K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

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Diode, Brems-Chopper / Diode, Brake-Chopper
Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	200	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	400	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	7500 6500	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,65 1,65 1,65	2,10	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 200\text{ A}, -di_F/dt = 4250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	185 210 215		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 200\text{ A}, -di_F/dt = 4250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	18,0 35,0 40,0		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 200\text{ A}, -di_F/dt = 4250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	8,30 15,5 17,5		mJ mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		0,215	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,0755		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

Diode, Revers / Diode, Reverse

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	25	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	50	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	90,0 75,0	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,75 1,75 1,75	2,25	V V V
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		1,30	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,125		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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NTC-Widerstand / NTC-Thermistor
Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_C = 25^\circ\text{C}$	R_{25}		5,00		k Ω
Abweichung von R100 Deviation of R100	$T_C = 100^\circ\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung Power dissipation	$T_C = 25^\circ\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/100}$		3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

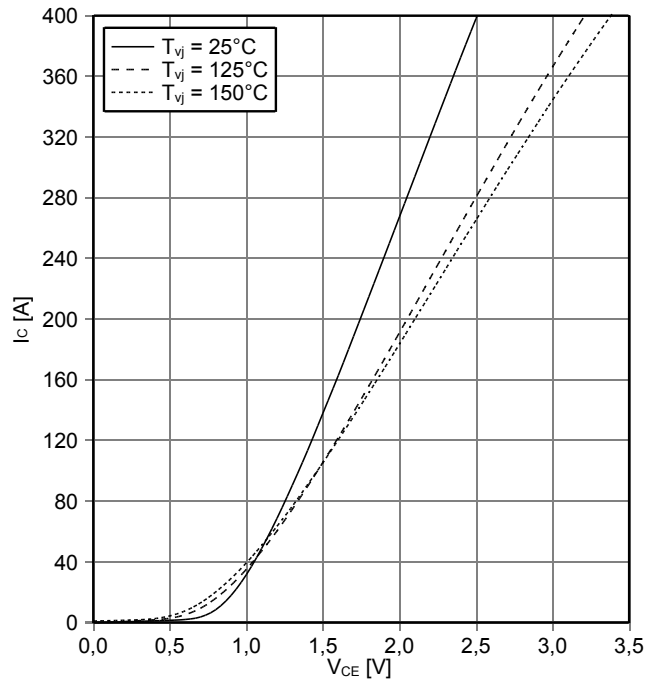
Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		2,5		kV
Material Modulgrundplatte Material of module baseplate				Cu		
Innere Isolation Internal isolation	Basisisolation (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)			Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			15,0 12,5		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			11,0 7,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
Modulstreuintuktivität Stray inductance module		L_{sCE}		20		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	$T_C = 25^\circ\text{C}$, pro Schalter / per switch	$R_{\text{CC+EE}}$		1,40		m Ω
Lagertemperatur Storage temperature		T_{stg}	-40		125	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00	Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note	M	3,0	-	6,0	Nm
Gewicht Weight		G		400		g

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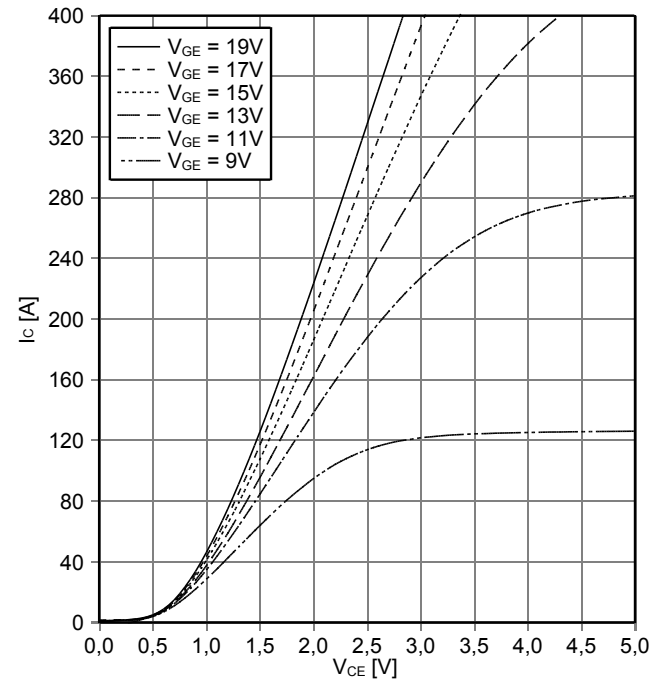
Ausgangskennlinie IGBT, Brems-Chopper (typisch)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



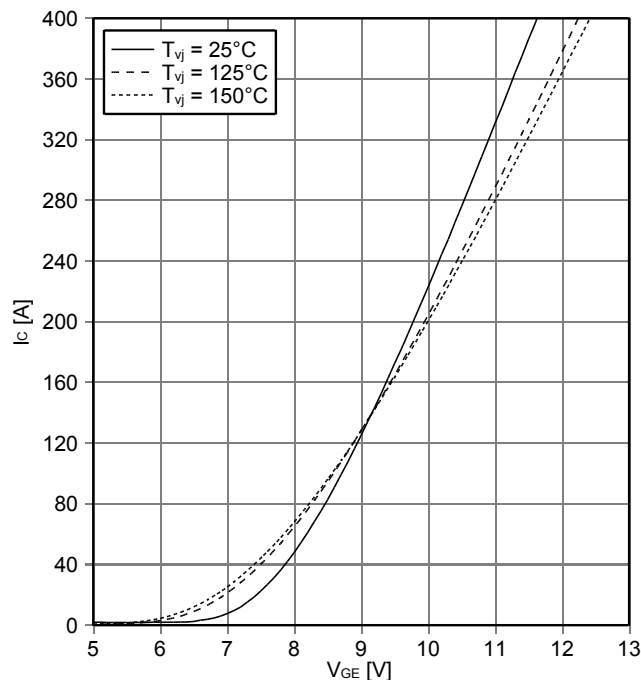
Ausgangskennlinienfeld IGBT, Brems-Chopper (typisch)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



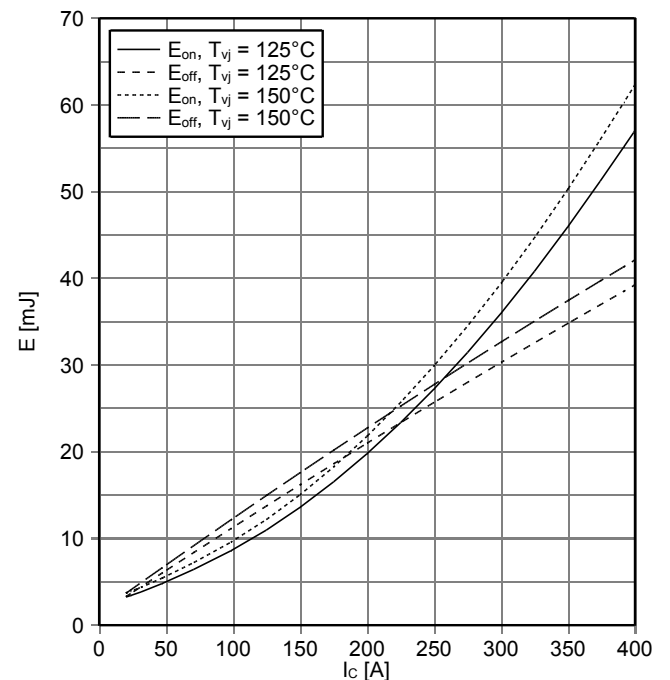
Übertragungscharakteristik IGBT, Brems-Chopper (typisch)
transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT, Brems-Chopper (typisch)
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 1\ \Omega, R_{Goff} = 1\ \Omega, V_{CE} = 600\text{ V}$

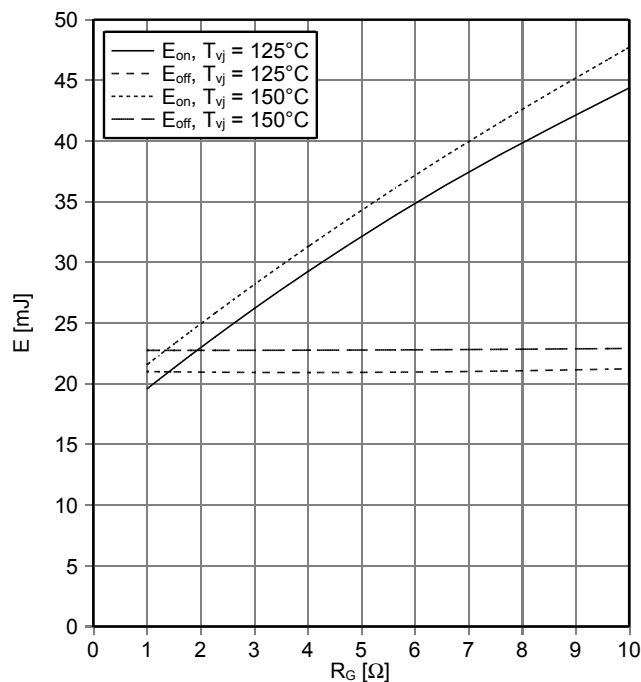


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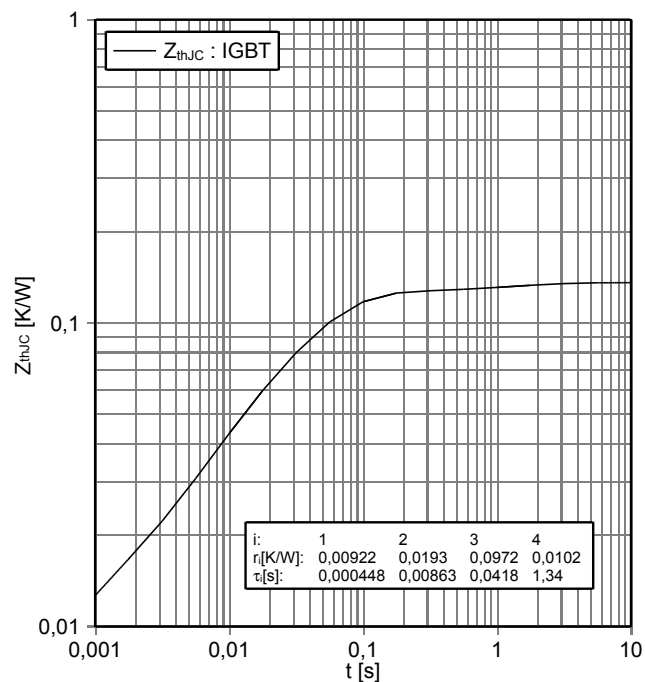
Schaltverluste IGBT, Brems-Chopper (typisch)
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 200\text{ A}, V_{CE} = 600\text{ V}$



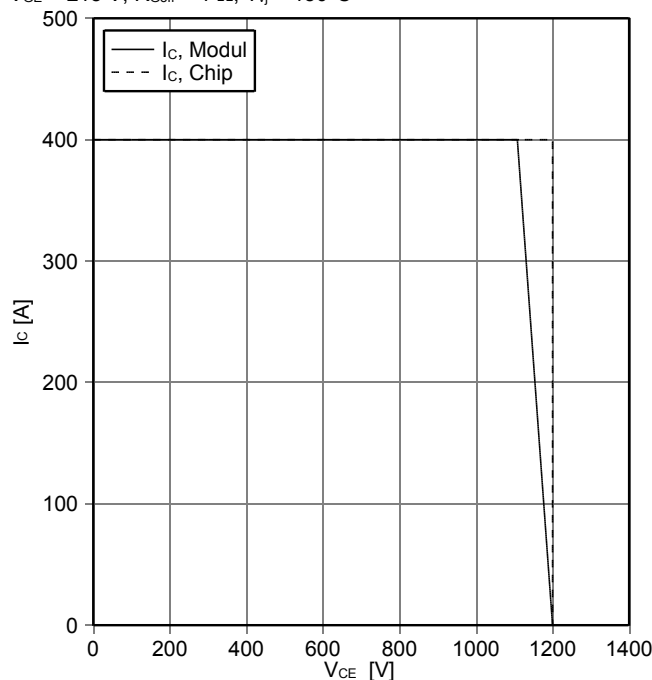
Transienter Wärmewiderstand IGBT, Brems-Chopper
transient thermal impedance IGBT, Brake-Chopper

$Z_{thJC} = f(t)$



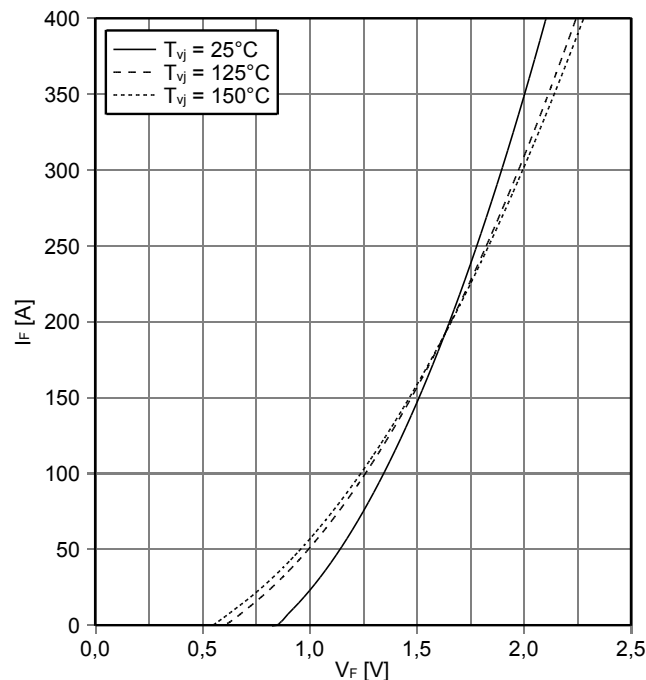
Sicherer Rückw.-Arbeitsber. IGBT, Brems-Chopper (RBSOA)
reverse bias safe operating area IGBT, Brake-Chopper (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 1\ \Omega, T_{vj} = 150^\circ\text{C}$



Durchlasskennlinie der Diode, Brems-Chopper (typisch)
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$

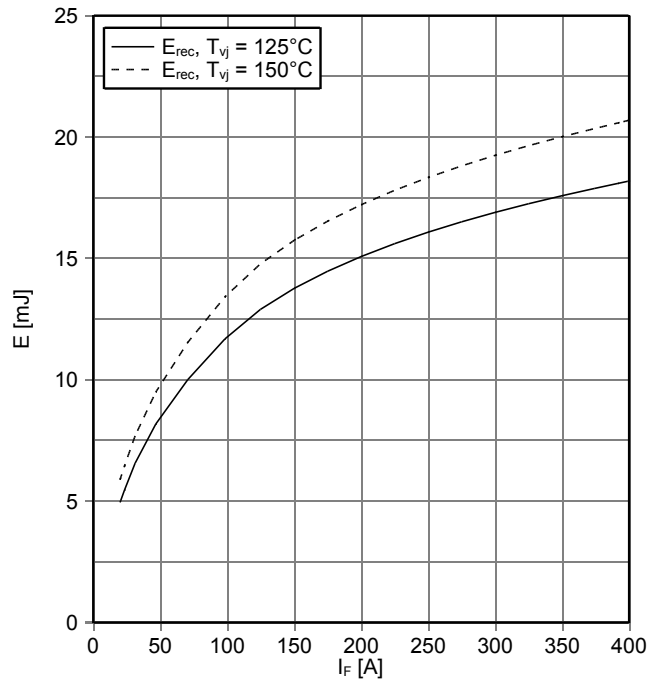


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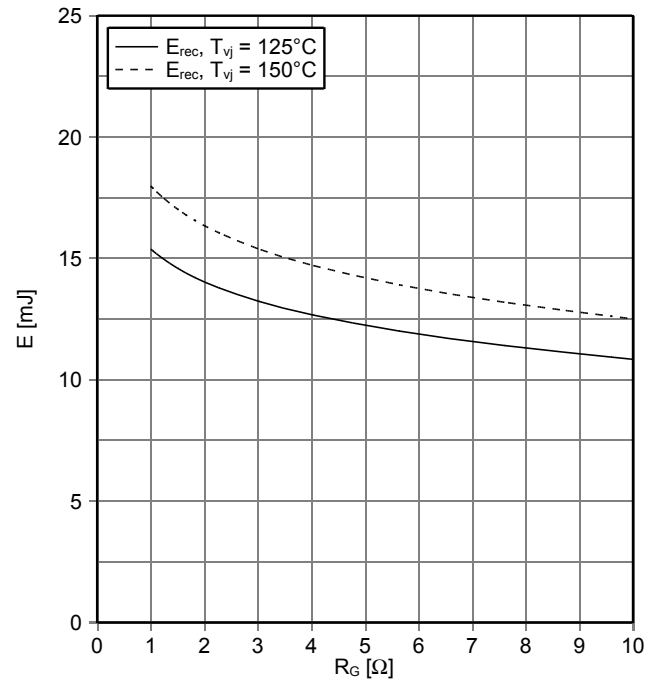
Schaltverluste Diode, Brems-Chopper (typisch)
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1 \Omega, V_{CE} = 600 V$



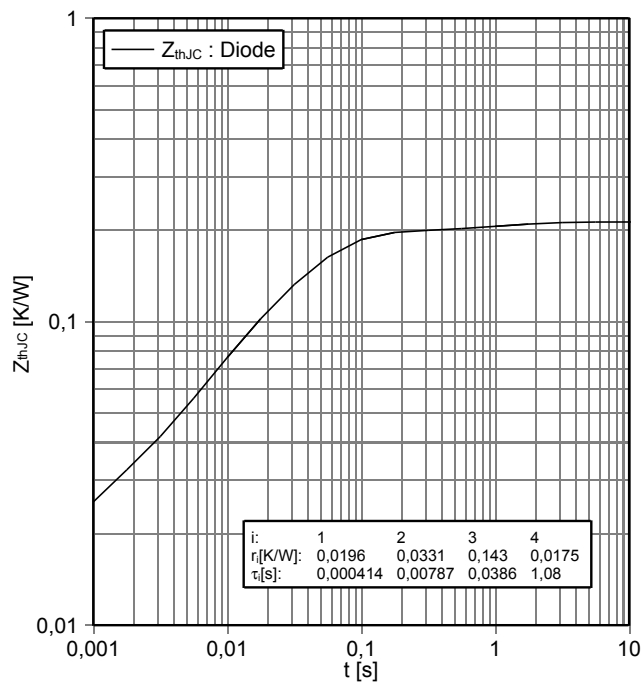
Schaltverluste Diode, Brems-Chopper (typisch)
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(R_G)$
 $I_F = 200 A, V_{CE} = 600 V$



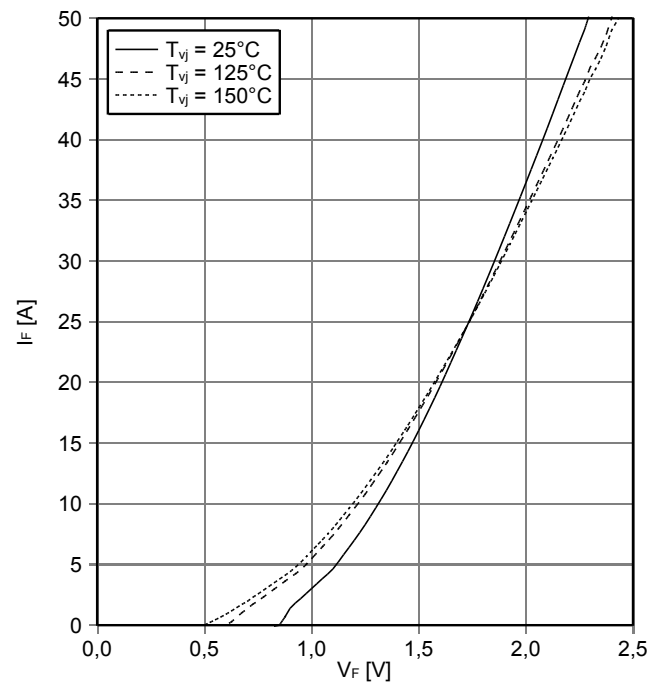
Transienter Wärmewiderstand Diode, Brems-Chopper
transient thermal impedance Diode, Brake-Chopper

$Z_{thJC} = f(t)$



Durchlasskennlinie der Diode, Revers (typisch)
forward characteristic of Diode, Reverse (typical)

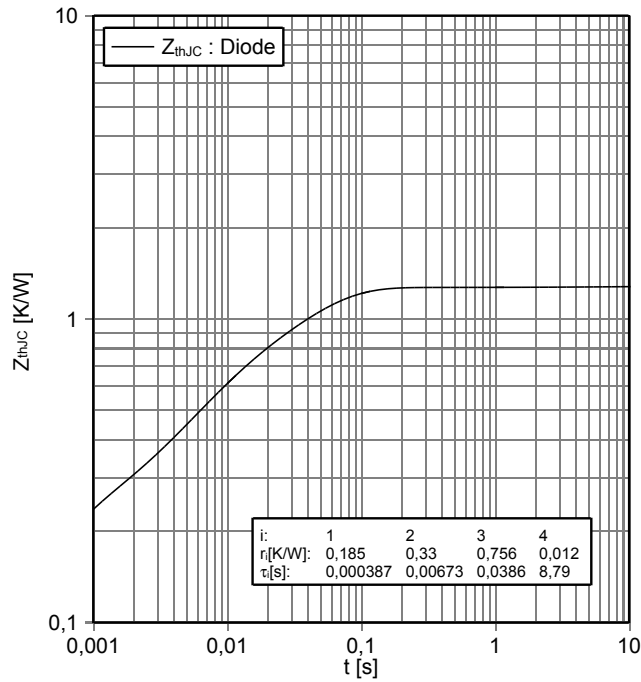
$I_F = f(V_F)$



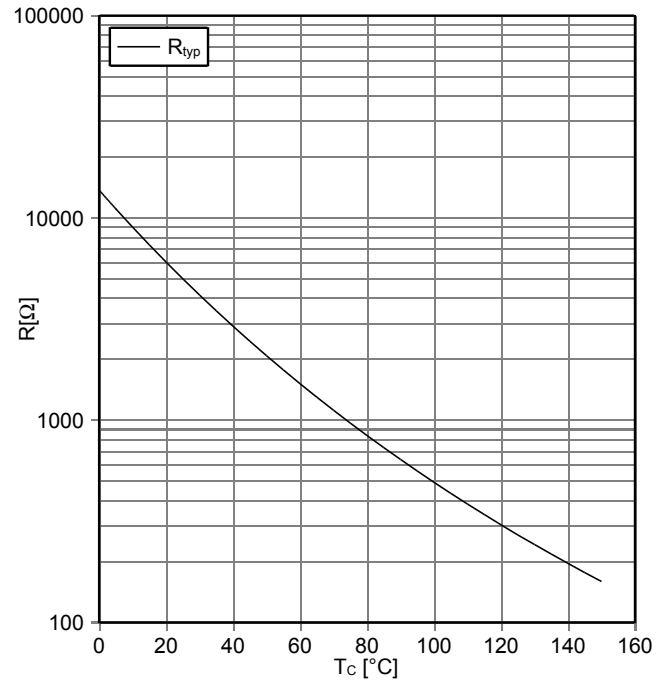
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Transienter Wärmewiderstand Diode, Revers
transient thermal impedance Diode, Reverse
 $Z_{thJC} = f(t)$

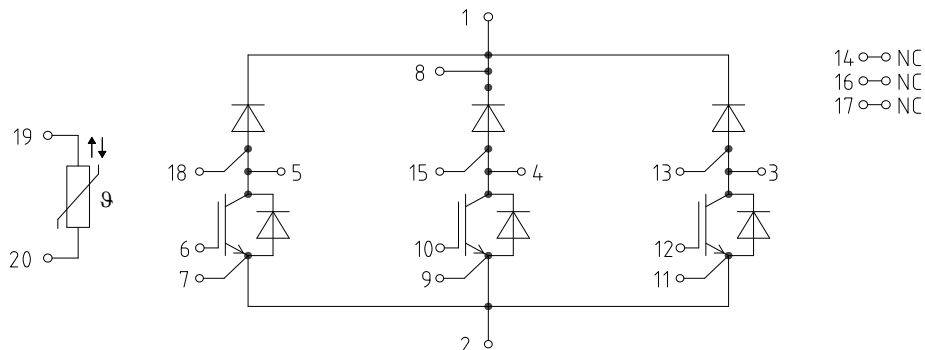


NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$

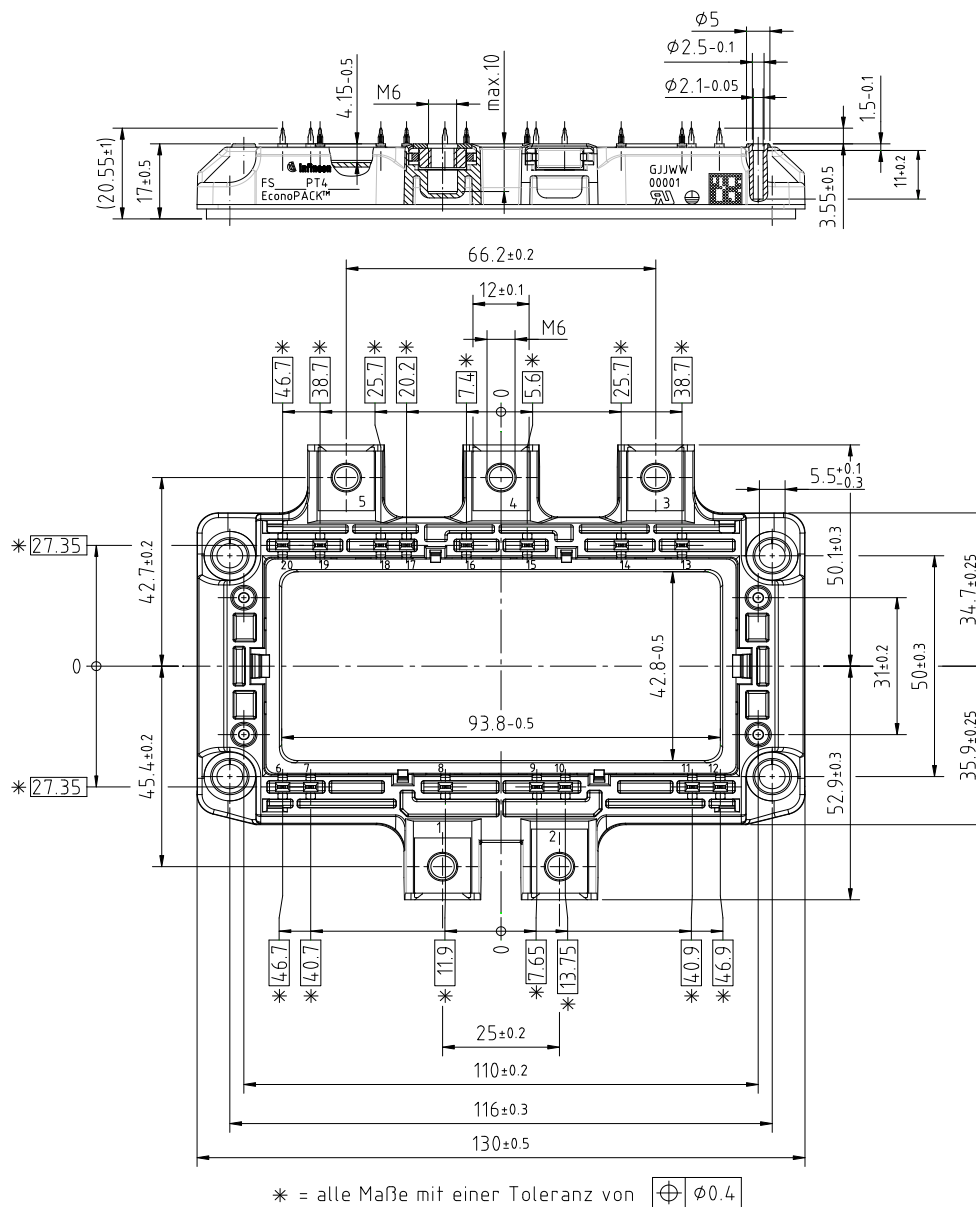


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Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



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